ABSTRACT OF THE DISCLOSURE

There is disclosed a semiconductor apparatus comprising a semiconductor substrate having a first region and a second region isolated from the first region, a first semiconductor device which is formed in the first region and which includes a first gate insulating film of a silicon oxide single film formed on the semiconductor substrate, and a first gate electrode formed on the first gate insulating film, and a second semiconductor device which is formed in the second region and which includes a second insulating film of a single layer made of an insulating material of a dielectric constant different from that of the silicon oxide film, and a second gate electrode formed on the second gate insulating film.